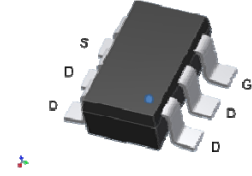
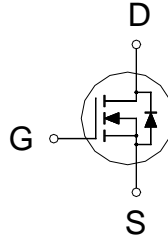


N-Channel Logic Level Enhancement Mode Field Effect Transistor

Product Summary:

BV_{DSS}	30V
$R_{DS(on)}$ (MAX.)	35m Ω
I_D	5.5A



Pb-Free Lead Plating & Halogen Free



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNIT
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	$T_A = 25^\circ\text{C}$	I_D	5.5	A
	$T_A = 70^\circ\text{C}$		3.6	
Pulsed Drain Current ¹		I_{DM}	22	
Power Dissipation	$T_A = 25^\circ\text{C}$	P_D	1.92	W
	$T_A = 70^\circ\text{C}$		1.23	
Operating Junction & Storage Temperature Range		T_{j}, T_{stg}	-55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNIT
Junction-to-Ambient ³	$R_{\theta JA}$ ($T \leq 10\text{sec}$)		65	$^\circ\text{C} / \text{W}$
	$R_{\theta JA}$ (Steady State)		100	

¹Pulse width limited by maximum junction temperature.

²Duty cycle $\leq 1\%$

³Pulse width limited by maximum junction temperature.

ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	30			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1.0	1.5	3.0	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0V, V _{GS} = ±20V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 24V, V _{GS} = 0V			1	μA
		V _{DS} = 20V, V _{GS} = 0V, T _J = 125 °C			10	
On-State Drain Current ¹	I _{D(ON)}	V _{DS} = 5V, V _{GS} = 10V	5.5			A
Drain-Source On-State Resistance ¹	R _{DS(ON)}	V _{GS} = 10V, I _D = 5.5A		30	35	mΩ
		V _{GS} = 4.5V, I _D = 4.5A		40	50	
Forward Transconductance ¹	g _{fs}	V _{DS} = 5V, I _D = 5.5A		11		S
DYNAMIC						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 10V, f = 1MHz		323		pF
Output Capacitance	C _{oss}			75		
Reverse Transfer Capacitance	C _{rss}			53		
Total Gate Charge ^{1,2}	Q _g	V _{DS} = 10V, V _{GS} = 10V, I _D = 5.5A		7.1		nC
Gate-Source Charge ^{1,2}	Q _{gs}			1.1		
Gate-Drain Charge ^{1,2}	Q _{gd}			2.2		
Turn-On Delay Time ^{1,2}	t _{d(on)}	V _{DS} = 15V, I _D = 1A, V _{GS} = 10V, R _{GS} = 6Ω		8		nS
Rise Time ^{1,2}	t _r			12		
Turn-Off Delay Time ^{1,2}	t _{d(off)}			28		
Fall Time ^{1,2}	t _f			15		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_C = 25 °C)						
Continuous Current	I _S				2	A
Pulsed Current ³	I _{SM}				8	
Forward Voltage ¹	V _{SD}	I _F = I _S , V _{GS} = 0V			1.2	V

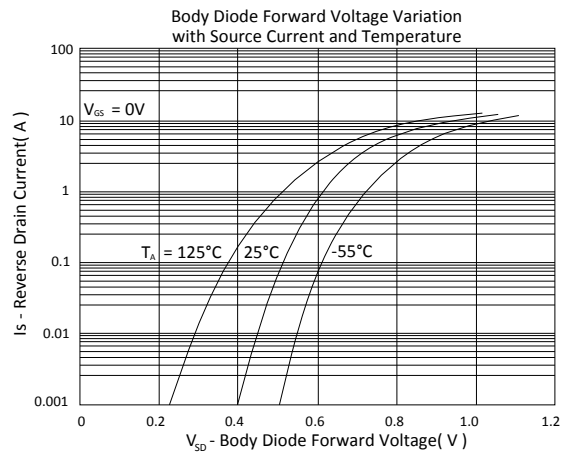
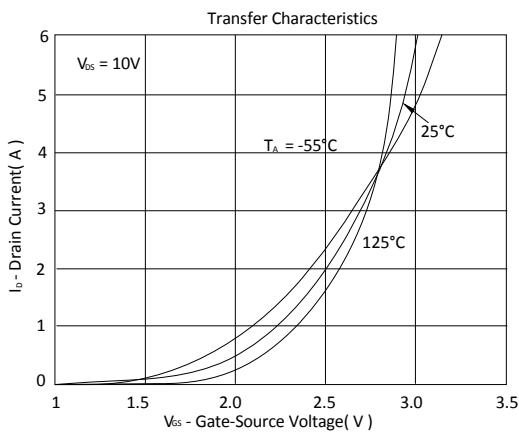
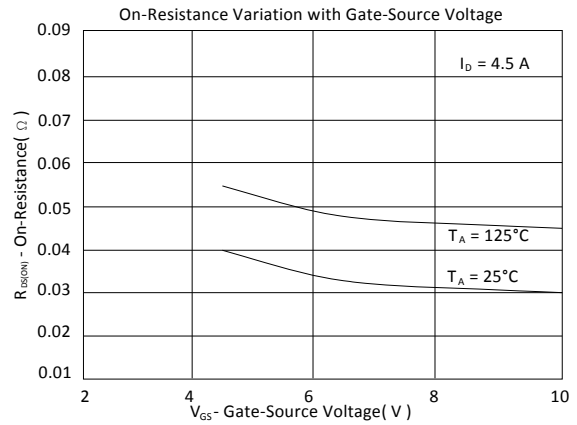
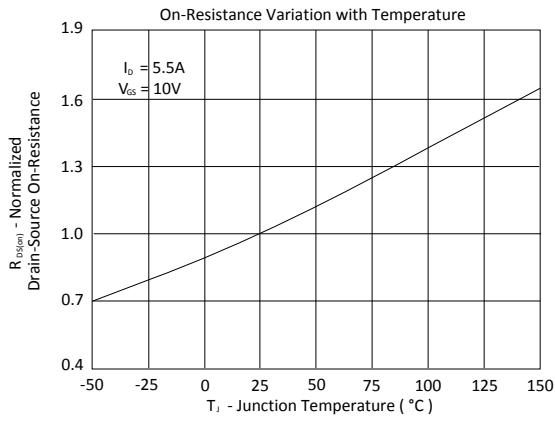
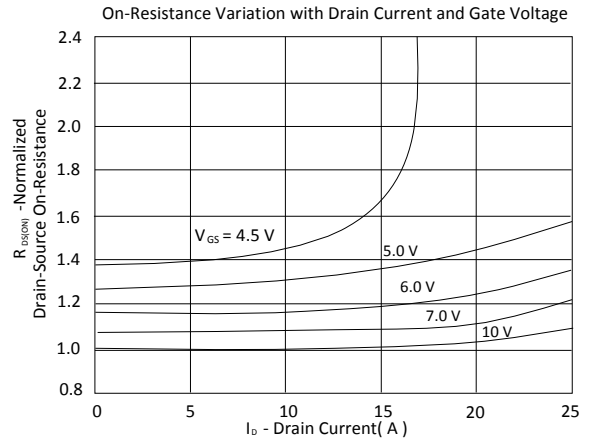
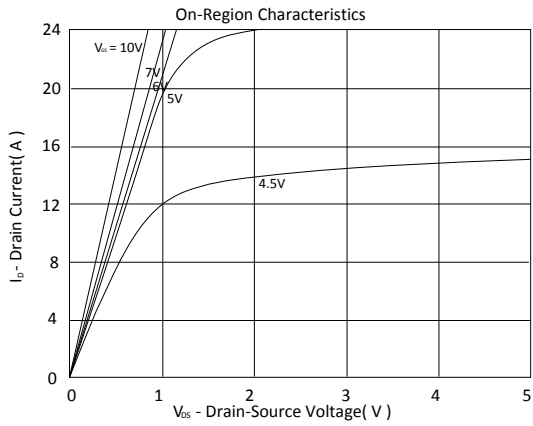
¹Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

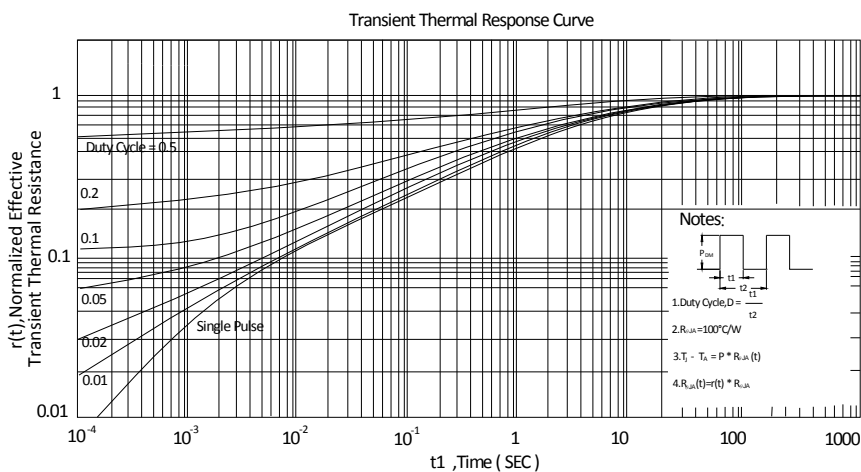
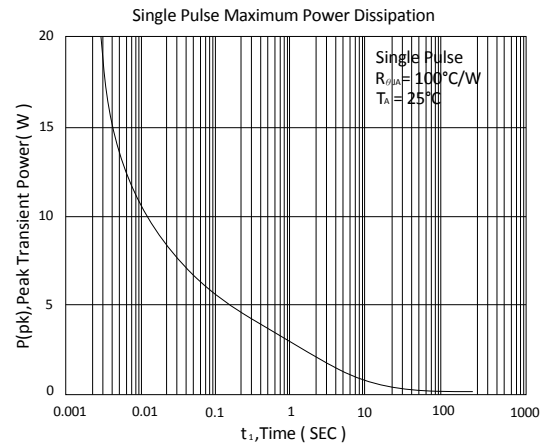
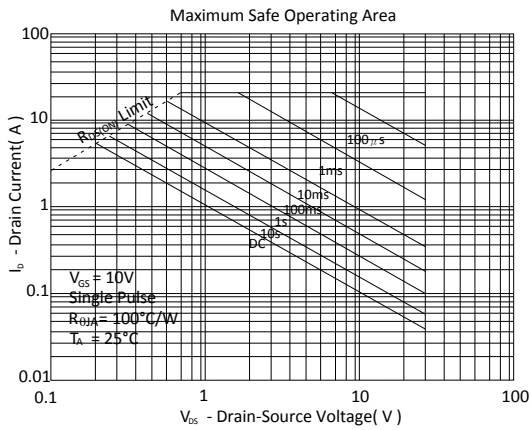
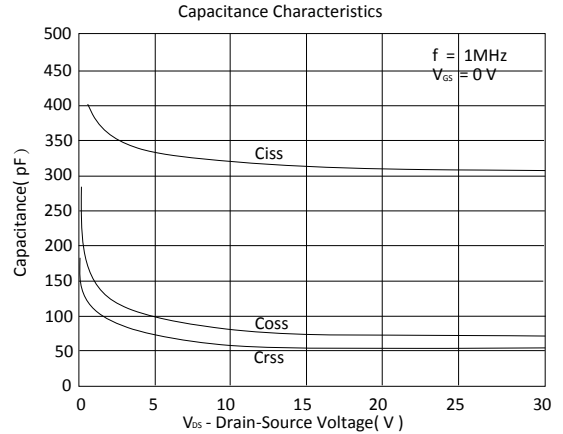
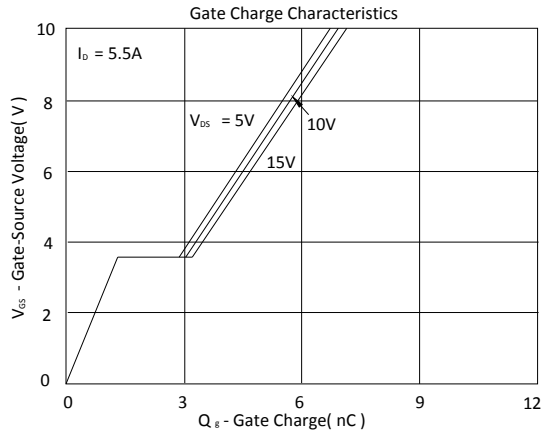
²Independent of operating temperature.

³Pulse width limited by maximum junction temperature.



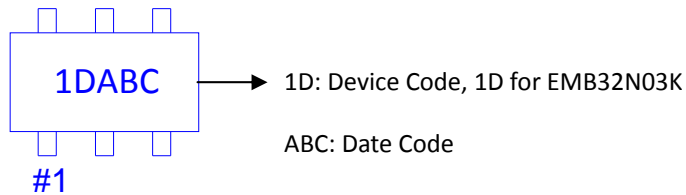
TYPICAL CHARACTERISTICS



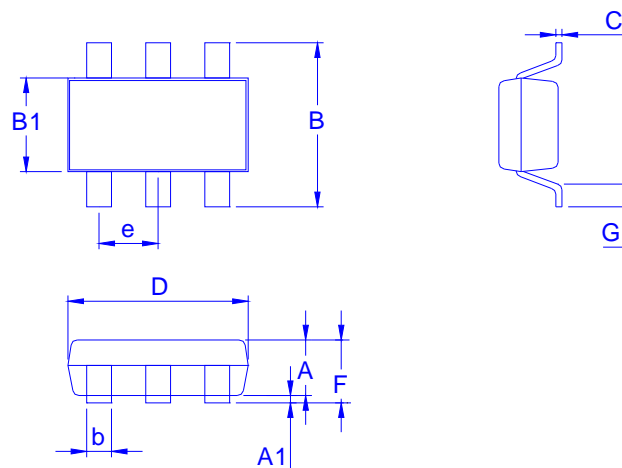


Ordering & Marking Information:

Device Name: EMB32N03K for TSOP-6



Outline Drawing



Dimension in mm

Dimension	A	A1	B	B1	b	C	D	e	F	G
Min.	0.70	0	2.50	1.50	0.30	0.08	2.70		0.70	0.30
Typ.	0.95		2.80	1.60	0.40		2.90	0.95		
Max.	1.00	0.10	3.10	1.70	0.50	0.20	3.10		1.10	0.60

Footprint

